

PATENT ASSIGNMENT COVER SHEET

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SUBMISSION TYPE:	NEW ASSIGNMENT	
NATURE OF CONVEYANCE:	ASSIGNMENT	
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	Name	Execution Date
	TOSHIBA TECHNO CENTER INC.	08/29/2014
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	Property Type	Number
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DATE SIGNED:	09/08/2014	
Total Attachments: 4		
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PATENT ASSIGNMENT

For good and valuable consideration, the receipt of which is hereby acknowledged, and subject to the reservations of certain non-exclusive rights and licenses stated in a separate written agreement between the parties dated 5 May 2014, **Toshiba Techno Center Inc.**, a Corporation organized under the laws of Japan, having its principal place of business at 12-1 Ekimae-Honcho, Kawasaki-ku, Kawasaki-shi, Kanagawa 210-0007, JAPAN (hereinafter "ASSIGNOR"), hereby grants and assigns to **Manutius IP, Inc.**, a Corporation organized under the laws of United States of America having its principal place of business at 101 First Street, Suite 549, Los Altos, CA 94022, United States of America, (hereinafter "ASSIGNEE"), all right, title and interest in and to the United States Letters Patent and applications for United States Letters Patent identified in Appendix A hereto, and all extensions, continuations, continuations in part, renewals, reissues, reexaminations and foreign counterparts thereto owned by ASSIGNOR (except to the extent otherwise agreed in writing by ASSIGNOR and ASSIGNEE) and the right to apply for any of the foregoing (hereinafter "ASSIGNED PATENTS"), to have and to hold the same, unto ASSIGNEE for its own use and enjoyment and for the use and enjoyment of its successors and assigns, for the full term or terms of all such rights, including but not limited to the right to sue for and recover damages for any past, present or future infringement of ASSIGNED PATENTS, subject to certain pre-existing non-exclusive rights, licenses and commitments that have been granted or made under or with respect to the ASSIGNED PATENTS before 5 May 2014 as set forth in the separate written agreement referenced above.

ASSIGNOR hereby authorizes that all ASSIGNED PATENTS to be issued on or resulting from any of the aforementioned applications for Letters Patent be issued to the ASSIGNEE.

ASSIGNOR hereby reserves and retains, for the benefit of itself and its subsidiary and affiliated companies and its and their successors or assigns, certain non-exclusive rights and licenses set forth in the separate written agreement referenced above.

IN WITNESS WHEREOF, ASSIGNOR has caused this Patent Assignment to be duly signed on its behalf.

SIGNATURE: Toshi Tsuda

NAME (Type or Print): Yoshiaki Tsuda

TITLE: President

DATE: Aug 29, 2014

Schedule 1 to Patent Assignment

No	Title	Application Number	Application Date	Patent Number	Issue Date
1	Light Emitting Diodes With Smooth Surface for Reflective Electrode	12/120,051	13-May-2008	7,781,780	Aug 24, 2010
2	Light Emitting Diodes With Smooth Surface for Reflective Electrode	12/834,747	12-Jul-2010	8,163,578	Apr 24, 2012
3	Light Emitting Diodes With Smooth Surface for Reflective Electrode	13/033,533	23-Feb-2011	8,168,984	May 1, 2012
4	Light Emitting Diodes With Smooth Surface for Reflective Electrode	13/447,574	16-Apr-2012	8,691,606	Apr 8, 2014
5	Light Emitting Diodes With Smooth Surface for Reflective Electrode	14/085,581 (Con of 13/447,574)	20-Nov-2013	N/A	N/A
6	Nucleation of Aluminum Nitride on a Silicon Substrate Using an Ammonia Preflow	13/190,420	25-Jul-2011	N/A	N/A
7	Non-Reactive Barrier Metal for Eutectic Bonding Process	13/196,870	2-Aug-2011	N/A	N/A
8	P-Type Doping Layers for Use with Light Emitting Devices	13/248,821	29-Sep-2011	8,698,163	Apr 15, 2014
9	P-Type Doping Layers for Use with Light Emitting Devices	14/158,471 (Con of 14/133,162 (Div of 13/248,821))	17-Jan-2014	N/A	N/A
10	P-Type Doping Layers for Use with Light Emitting Devices	14/133,162 (Div of 13/248,821)	18-Dec-2013	N/A	N/A
11	Light Emitting Devices Having Dislocation Density Maintaining Buffer Layers	13/249,157	29-Sep-2011	N/A	N/A
12	Light Emitting Devices Having Dislocation Density Maintaining Buffer Layers	14/158,401 (Con of 13/249,157)	17-Jan-2014	N/A	N/A
13	Light Emitting Devices Having Light Coupling Layers with Recessed Electrodes	13/249,196	29-Sep-2011	8,664,679	March 4, 2014
14	Light Emitting Devices Having Light Coupling Layers with	14/155,090	14-Jan-2014	N/A	N/A

	Recessed Electrodes				
15	Series Connected Segmented LED	13/292,938	9-Nov-2011	8,581,267	November 12, 2013
16	Series Connected Segmented LED	13/959,313 (Con of 13/292,938)	5-Aug-2013	N/A	N/A
17	III-Nitride Based Semiconductor Device With Low-Resistance Ohmic Contacts	10/936,496	9-Sep-2004	7,943,949	May 17, 2011
18	GaN Based LED Having Reduced Thickness And Method For Making The Same	11/761,223	11-Jun-2007	7,791,090	Sep 7, 2010
19	GaN Based LED Having Reduced Thickness And Method For Making The Same	12/860,162	20-Aug-2010	8,384,099	Feb 26, 2013
20	GaN Based LED Having Reduced Thickness And Method For Making The Same	13/754,517	30-Jan-2013	N/A	N/A